

Bo Shen

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8515528/publications.pdf>

Version: 2024-02-01

146
papers

3,354
citations

147566

31
h-index

182168

51
g-index

146
all docs

146
docs citations

146
times ranked

4443
citing authors

#	ARTICLE	IF	CITATIONS
1	Utilization of far-red LED to minimize blue light hazard for dynamic semiconductor lighting. LEUKOS - Journal of Illuminating Engineering Society of North America, 2023, 19, 53-70.	1.5	5
2	Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-7.	1.9	1
3	Lattice Polarity Manipulation of Quasi-2D Epitaxial GaN Films on Graphene Through Interface Atomic Configuration. Advanced Materials, 2022, 34, e2106814.	11.1	19
4	Effect of unintentional nitrogen incorporation on n-type doping of $\text{In}^{2+}\text{-Ga}_2\text{O}_3$ grown by molecular beam epitaxy. CrystEngComm, 2022, 24, 269-274.	1.3	6
5	Lattice Polarity Manipulation of Quasi-2D Epitaxial GaN Films on Graphene Through Interface Atomic Configuration (Adv. Mater. 5/2022). Advanced Materials, 2022, 34, .	11.1	0
6	Polarization-Driven Orientation Selective Growth of Single-Crystalline III-Nitride Semiconductors on Arbitrary Substrates. Advanced Functional Materials, 2022, 32, .	7.8	6
7	Sub-nanometer ultrathin epitaxy of AlGaIn and its application in efficient doping. Light: Science and Applications, 2022, 11, 71.	7.7	22
8	Deep-Ultraviolet Micro-LEDs Exhibiting High Output Power and High Modulation Bandwidth Simultaneously. Advanced Materials, 2022, 34, e2109765.	11.1	33
9	Polarization-Driven Orientation Selective Growth of Single-Crystalline III-Nitride Semiconductors on Arbitrary Substrates (Adv. Funct. Mater. 14/2022). Advanced Functional Materials, 2022, 32, .	7.8	0
10	Gate/Drain Coupled Barrier Lowering Effect and Negative Threshold Voltage Shift in Schottky-Type p-GaN Gate HEMT. IEEE Transactions on Electron Devices, 2022, 69, 3630-3635.	1.6	10
11	Wide bandgap semiconductor materials and devices. Journal of Applied Physics, 2022, 131, .	1.1	12
12	Influence of intrinsic or extrinsic doping on charge state of carbon and its interaction with hydrogen in GaN. Applied Physics Letters, 2022, 120, .	1.5	2
13	Improvement in Modulation Bandwidth of Micro-LED Arrays Based on Low-Temperature-Interlayer Approach. IEEE Photonics Technology Letters, 2022, 34, 675-678.	1.3	1
14	Low ON-Resistance Fully-Vertical GaN-on-SiC Schottky Barrier Diode with Conductive Buffer Layer. , 2022, , .		1
15	Low-Resistive Ohmic Contacts in High-Electron-Mobility AlN/GaN Heterostructures by Suppressing the Oxygen Incorporation. ACS Applied Electronic Materials, 2022, 4, 3632-3639.	2.0	2
16	Controlling Phase-Coherent Electron Transport in III-Nitrides: Toward Room Temperature Negative Differential Resistance in AlGaIn/GaN Double Barrier Structures. Advanced Functional Materials, 2021, 31, 2007216.	7.8	12
17	Realization of high efficiency AlGaIn-based multiple quantum wells grown on nano-patterned sapphire substrates. CrystEngComm, 2021, 23, 1201-1206.	1.3	14
18	Epitaxial growth mechanisms of single-crystalline GaN on single-crystalline graphene. CrystEngComm, 2021, 23, 5451-5455.	1.3	5

#	ARTICLE	IF	CITATIONS
19	Deep subwavelength control of valley polarized cathodoluminescence in h-BN/WSe ₂ /h-BN heterostructure. <i>Nature Communications</i> , 2021, 12, 291.	5.8	25
20	High quality GaN-on-SiC with low thermal boundary resistance by employing an ultrathin AlGaN buffer layer. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	12
21	Electrical Spin Injection into the 2D Electron Gas in AlN/GaN Heterostructures with Ultrathin AlN Tunnel Barrier. <i>Advanced Functional Materials</i> , 2021, 31, 2009771.	7.8	11
22	Selectively steering photon spin angular momentum via electron-induced optical spin Hall effect. <i>Science Advances</i> , 2021, 7, .	4.7	17
23	Suppressing Buffer-Induced Current Collapse in GaN HEMTs with a Source-Connected p-GaN (SCPG): A Simulation Study. <i>Electronics (Switzerland)</i> , 2021, 10, 942.	1.8	5
24	Control of dislocations in heteroepitaxial AlN films by extrinsic supersaturated vacancies introduced through thermal desorption of heteroatoms. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	11
25	Low-Defect-Density Aluminum Nitride (AlN) Thin Films Realized by Zigzag Macrostep-Induced Dislocation Redirection. <i>Crystal Growth and Design</i> , 2021, 21, 3394-3400.	1.4	9
26	High-mobility n ⁺ -GaN drift layer grown on Si substrates. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	5
27	Spin dynamics in GaN/Al _{0.1} Ga _{0.9} N quantum well with complex band edge structure. <i>Applied Physics Letters</i> , 2021, 118, 252107.	1.5	4
28	The effects of dynamic daylight-like light on the rhythm, cognition, and mood of irregular shift workers in closed environment. <i>Scientific Reports</i> , 2021, 11, 13059.	1.6	10
29	Hydrogen-Modulated Step Graded Junction Termination Extension in GaN Vertical p-n Diodes. <i>IEEE Electron Device Letters</i> , 2021, 42, 1124-1127.	2.2	11
30	Excitonic effects on electron spin orientation and relaxation in wurtzite GaN. <i>Physical Review B</i> , 2021, 104, .	1.1	3
31	Study on Localized Surface Plasmon Coupling with Many Radiators. <i>Nanomaterials</i> , 2021, 11, 3105.	1.9	5
32	Direct-readout pressure sensor based on AlGaIn/GaN heterostructure. <i>Microsystem Technologies</i> , 2020, 26, 3189-3192.	1.2	0
33	Graphene Acoustic Phonon-Mediated Pseudo-Landau Levels Tailoring Probed by Scanning Tunneling Spectroscopy. <i>Small</i> , 2020, 16, 1905202.	5.2	2
34	Three Subband Occupation of the Two-Dimensional Electron Gas in Ultrathin Barrier AlN/GaN Heterostructures. <i>Advanced Functional Materials</i> , 2020, 30, 2004450.	7.8	11
35	Direct evidence of hydrogen interaction with carbon: C-H complex in semi-insulating GaN. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	12
36	High quality AlN film grown on a nano-concave-circle patterned Si substrate with an AlN seed layer. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	13

#	ARTICLE	IF	CITATIONS
37	Role of the Exciton-Polariton in a Continuous-Wave Optically Pumped CsPbBr ₃ Perovskite Laser. Nano Letters, 2020, 20, 6636-6643.	4.5	145
38	Investigation of carrier compensation traps in n-GaN drift layer by high-temperature deep-level transient spectroscopy. Applied Physics Letters, 2020, 117, .	1.5	7
39	High Voltage Vertical GaN-on-GaN Schottky Barrier Diode with High Energy Fluorine Ion Implantation Based on Space Charge Induced Field Modulation (SCIFM) Effect. , 2020, , .		9
40	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	7.7	20
41	Spontaneous Emission of Plasmon-Exciton Polaritons Revealed by Ultrafast Nonradiative Decays. Laser and Photonics Reviews, 2020, 14, 2000233.	4.4	8
42	Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. Applied Physics Letters, 2020, 117, 133106.	1.5	3
43	The in-plane anisotropy of the effective g factors in Al _{0.25} Ga _{0.75} N/GaN based quantum point contacts with narrow channels. Applied Physics Letters, 2020, 116, 182101.	1.5	1
44	Study on Electron-Induced Surface Plasmon Coupling with Quantum Well Using a Perturbation Method. Nanomaterials, 2020, 10, 913.	1.9	5
45	Spin relaxation induced by interfacial effects in n-GaN/MgO/Co spin injectors. RSC Advances, 2020, 10, 12547-12553.	1.7	7
46	Al diffusion at AlN/Si interface and its suppression through substrate nitridation. Applied Physics Letters, 2020, 116, .	1.5	23
47	Single-Photon Emission from Point Defects in Aluminum Nitride Films. Journal of Physical Chemistry Letters, 2020, 11, 2689-2694.	2.1	35
48	Graphene-Assisted Epitaxy of Nitrogen Lattice Polarity GaN Films on Non-Polar Sapphire Substrates for Green Light Emitting Diodes. Advanced Functional Materials, 2020, 30, 2001283.	7.8	41
49	Interface charge engineering in down-scaled AlGaIn ($\sim 6\text{ nm}$)/GaN heterostructure for fabrication of GaN-based power HEMTs and MIS-HEMTs. Applied Physics Letters, 2020, 116, .	1.5	20
50	Strain-enhanced high Q-factor GaN micro-electromechanical resonator. Science and Technology of Advanced Materials, 2020, 21, 515-523.	2.8	11
51	Quasi-Vertical GaN Schottky Barrier Diode on Silicon Substrate With 10^{10} High On/Off Current Ratio and Low Specific On-Resistance. IEEE Electron Device Letters, 2020, 41, 329-332.	2.2	51
52	Investigation on entraining and enhancing human circadian rhythm in closed environments using daylight-like LED mixed lighting. Science of the Total Environment, 2020, 732, 139334.	3.9	33
53	Vacancy-engineering-induced dislocation inclination in III-nitrides on Si substrates. Physical Review Materials, 2020, 4, .	0.9	20
54	Many-body Effects on the High Injection Level Performance for Micro Light Emitting Diode. , 2020, , .		0

#	ARTICLE	IF	CITATIONS
55	High-Performance Quasi-Vertical GaN Schottky Barrier Diode on Silicon Substrate with a Low Dislocation Density Drift Layer. , 2019, , .		2
56	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. Applied Physics Letters, 2019, 115, .	1.5	11
57	Epitaxy of Singleâ€Crystalline GaN Film on CMOSâ€Compatible Si(100) Substrate Buffered by Graphene. Advanced Functional Materials, 2019, 29, 1905056.	7.8	51
58	Inversion Symmetry Breaking Induced Valley Hall Effect in Multilayer WSe₂. ACS Nano, 2019, 13, 9325-9331.	7.3	19
59	Impact of Silicon Substrate with Low Resistivity on Vertical Leakage Current in AlGaN/GaN HEMTs. Applied Sciences (Switzerland), 2019, 9, 2373.	1.3	3
60	Experimental Evidence of Large Bandgap Energy in Atomically Thin AlN. Advanced Functional Materials, 2019, 29, 1902608.	7.8	21
61	GaNâ€onâ€Si(100): Epitaxy of Singleâ€Crystalline GaN Film on CMOSâ€Compatible Si(100) Substrate Buffered by Graphene (Adv. Funct. Mater. 42/2019). Advanced Functional Materials, 2019, 29, 1970293.	7.8	1
62	Planar anisotropic Shubnikov-de-Haas oscillations of two-dimensional electron gas in AlN/GaN heterostructure. Applied Physics Letters, 2019, 115, 152107.	1.5	5
63	Dominant Influence of Interface Roughness Scattering on the Performance of GaN Terahertz Quantum Cascade Lasers. Nanoscale Research Letters, 2019, 14, 206.	3.1	11
64	Singleâ€photon emission from a further confined InGaN/GaN quantum disc via reverseâ€reaction growth. Quantum Engineering, 2019, 1, e20.	1.2	18
65	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. Advanced Optical Materials, 2019, 7, 1801763.	3.6	43
66	Fabrication of nano-patterned sapphire substrates by combining nanoimprint lithography with edge effects. CrystEngComm, 2019, 21, 1794-1800.	1.3	8
67	Study on 3D thermal transport in micro-LEDs on GaN substrate at the level of kW/cm². , 2019, , .		0
68	Multi-chip dynamic white light emitting diode with high level photobiological safety and good color fidelity. , 2019, , .		2
69	Self-Learning Perfect Optical Chirality via a Deep Neural Network. Physical Review Letters, 2019, 123, 213902.	2.9	72
70	Repeatable Room Temperature Negative Differential Resistance in AlN/GaN Resonant Tunneling Diodes Grown on Sapphire. Advanced Electronic Materials, 2019, 5, 1800651.	2.6	32
71	Ultrathin-Barrier AlGaN/GaN Heterostructure: A Recess-Free Technology for Manufacturing High-Performance GaN-on-Si Power Devices. IEEE Transactions on Electron Devices, 2018, 65, 207-214.	1.6	87
72	Plasmonicâ€Functionalized Broadband Perovskite Photodetector. Advanced Optical Materials, 2018, 6, 1701271.	3.6	86

#	ARTICLE	IF	CITATIONS
73	Vertical leakage induced current degradation and relevant traps with large lattice relaxation in AlGa _{0.2} N/GaN heterostructures on Si. Applied Physics Letters, 2018, 112, 032104.	1.5	8
74	High-electron-mobility InN epilayers grown on silicon substrate. Applied Physics Letters, 2018, 112, .	1.5	22
75	Low ON-Resistance GaN Schottky Barrier Diode With High V_{ON} Uniformity Using LPCVD Si ₃ N ₄ Compatible Self-Terminated, Low Damage Anode Recess Technology. IEEE Electron Device Letters, 2018, 39, 859-862.	2.2	44
76	Characterization of 880 V Normally Off GaN MOSHEMT on Silicon Substrate Fabricated With a Plasma-Free, Self-Terminated Gate Recess Process. IEEE Transactions on Electron Devices, 2018, 65, 1453-1457.	1.6	43
77	A study of GaN nucleation and coalescence in the initial growth stages on nanoscale patterned sapphire substrates via MOCVD. CrystEngComm, 2018, 20, 6811-6820.	1.3	26
78	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. Physical Review Letters, 2018, 121, 145505.	2.9	45
79	High-Quality AlN Film Grown on Sputtered AlN/Sapphire via Growth-Mode Modification. Crystal Growth and Design, 2018, 18, 6816-6823.	1.4	45
80	Measurement of the Transport Property of 2-DEG in AlGa _{0.2} N/GaN Heterostructures Based on Circular Transmission Line Modeling of Two Concentric-Circle Schottky Contacts. IEEE Transactions on Electron Devices, 2018, 65, 3163-3168.	1.6	1
81	Tailoring MoS ₂ Valley-Polarized Photoluminescence with Super Chiral Near-Field. Advanced Materials, 2018, 30, e1801908.	11.1	99
82	Study on the Coupling Mechanism of the Orthogonal Dipoles with Surface Plasmon in Green LED by Cathodoluminescence. Nanomaterials, 2018, 8, 244.	1.9	6
83	Enhanced Hydrogen Detection Based on Mg-Doped InN Epilayer. Sensors, 2018, 18, 2065.	2.1	1
84	Gate-Recessed Normally OFF GaN MOSHEMT With High-Temperature Oxidation/Wet Etching Using LPCVD Si ₃ N ₄ as the Mask. IEEE Transactions on Electron Devices, 2018, 65, 1728-1733.	1.6	31
85	Molecular beam epitaxy of single-crystalline aluminum film for low threshold ultraviolet plasmonic nanolasers. Applied Physics Letters, 2018, 112, .	1.5	15
86	Lattice-Symmetry-Driven Epitaxy of Hierarchical GaN Nanotripods. Advanced Functional Materials, 2017, 27, 1604854.	7.8	17
87	High quality AlN epilayers grown on nitrided sapphire by metal organic chemical vapor deposition. Scientific Reports, 2017, 7, 42747.	1.6	33
88	Exciton emission of quasi-2D InGa _{0.2} N in GaN matrix grown by molecular beam epitaxy. Scientific Reports, 2017, 7, 46420.	1.6	14
89	Enhanced transport properties in InAlGa _{0.2} N/AlN/GaN heterostructures on Si (111) substrates: The role of interface quality. Applied Physics Letters, 2017, 110, .	1.5	11
90	Flexibly and Repeatedly Modulating Lasing Wavelengths in a Single Core-Shell Semiconductor Microrod. ACS Nano, 2017, 11, 5808-5814.	7.3	26

#	ARTICLE	IF	CITATIONS
91	Magneto-transport Spectroscopy of the First and Second Two-dimensional Subbands in Al _{0.25} Ga _{0.75} N/GaN Quantum Point Contacts. Scientific Reports, 2017, 7, 42974.	1.6	3
92	Kilovolt GaN MOSHEMT on silicon substrate with breakdown electric field close to the theoretical limit. , 2017, , .		5
93	Improving Performance of Algan-Based Deep-Ultraviolet Light-Emitting Diodes by Inserting a Higher Al-Content Algan Layer Within the Multiple Quantum Wells. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700461.	0.8	4
94	Schottky-MOS Hybrid Anode AlGaIn/GaN Lateral Field-Effect Rectifier With Low Onset Voltage and Improved Breakdown Voltage. IEEE Electron Device Letters, 2017, 38, 1425-1428.	2.2	29
95	K^{\uparrow} crossover transition in the conduction band of monolayer MoS ₂ under hydrostatic pressure. Science Advances, 2017, 3, e1700162.	4.7	60
96	Gate-Recessed Normally-OFF GaN MOSHEMT With Improved Channel Mobility and Dynamic Performance Using AlN/Si ₃ N ₄ as Passivation and Post Gate-Recess Channel Protection Layers. IEEE Electron Device Letters, 2017, 38, 1075-1078.	2.2	19
97	Local surface plasmon enhanced polarization and internal quantum efficiency of deep ultraviolet emissions from AlGaIn-based quantum wells. Scientific Reports, 2017, 7, 2358.	1.6	18
98	Anomalous surface potential behavior observed in InN by photoassisted Kelvin probe force microscopy. Applied Physics Letters, 2017, 110, 222103.	1.5	3
99	Photon wavelength dependent valley photocurrent in multilayer $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \rangle \langle \text{mml:mrow} \langle \text{mml:mi} \rangle \text{MoS} \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \langle \text{mml:mn} \rangle 2 \langle \text{mml:mn} \rangle \rangle \rangle$ Physical Review B, 2017, 96, .		18
100	Anisotropic strain relaxation and high quality AlGaIn/GaN heterostructures on Si (110) substrates. Applied Physics Letters, 2017, 110, .	1.5	5
101	Circular photogalvanic effect in CdSe nanowires at room temperature. , 2016, , .		0
102	Hot electron induced non-saturation current behavior at high electric field in InAlN/GaN heterostructures with ultrathin barrier. Scientific Reports, 2016, 6, 37415.	1.6	6
103	Edge Dislocations Triggered Surface Instability in Tensile Epitaxial Hexagonal Nitride Semiconductor. ACS Applied Materials & Interfaces, 2016, 8, 34108-34114.	4.0	7
104	Mechanism of stress-driven composition evolution during hetero-epitaxy in a ternary AlGaIn system. Scientific Reports, 2016, 6, 25124.	1.6	25
105	Buffer-Induced Time-Dependent OFF-State Leakage in AlGaIn/GaN High Electron Mobility Transistors on Silicon. IEEE Transactions on Electron Devices, 2016, 63, 4860-4864.	1.6	6
106	The effects of nanocavity and photonic crystal in InGaIn/GaN nanorod LED arrays. Nanoscale Research Letters, 2016, 11, 340.	3.1	25
107	High-Output-Power Ultraviolet Light Source from Quasi-2D GaN Quantum Structure. Advanced Materials, 2016, 28, 7978-7983.	11.1	72
108	Study on Light Extraction from GaN-based Green Light-Emitting Diodes Using Anodic Aluminum Oxide Pattern and Nanoimprint Lithography. Scientific Reports, 2016, 6, 21573.	1.6	23

#	ARTICLE	IF	CITATIONS
109	High-quality AlN epitaxy on nano-patterned sapphire substrates prepared by nano-imprint lithography. Scientific Reports, 2016, 6, 35934.	1.6	110
110	Growth of high quality and uniformity AlGaIn/GaN heterostructures on Si substrates using a single AlGaIn layer with low Al composition. Scientific Reports, 2016, 6, 23020.	1.6	52
111	A GaN HEMT Structure Allowing Self-Terminated, Plasma-Free Etching for High-Uniformity, High-Mobility Enhancement-Mode Devices. IEEE Electron Device Letters, 2016, 37, 377-380.	2.2	52
112	Lattice-Polarity-Driven Epitaxy of Hexagonal Semiconductor Nanowires. Nano Letters, 2016, 16, 1328-1334.	4.5	35
113	Free and bound excitonic effects in Al _{0.5} Ga _{0.5} N/Al _{0.35} Ga _{0.65} N MQWs with different Si-doping levels in the well layers. Scientific Reports, 2015, 5, 13046.	1.6	20
114	Study on AlGaIn P-I-N-I-N solar-blind avalanche photodiodes with Al _{0.45} Ga _{0.55} N multiplication layer. Electronic Materials Letters, 2015, 11, 1053-1058.	1.0	10
115	Reduction of Current Collapse in GaN High-Electron Mobility Transistors Using a Repeated Ozone Oxidation and Wet Surface Treatment. IEEE Electron Device Letters, 2015, 36, 757-759.	2.2	19
116	Development trends of GaN-based wide bandgap semiconductors: from solid state lighting to power electronic devices. Frontiers of Optoelectronics, 2015, 8, 456-460.	1.9	13
117	Temperature Dependence of the Surface- and Buffer-Induced Current Collapse in GaN High-Electron Mobility Transistors on Si Substrate. IEEE Transactions on Electron Devices, 2015, 62, 2475-2480.	1.6	36
118	Formation of p-n-p junction with ionic liquid gate in graphene. Applied Physics Letters, 2014, 104, .	1.5	10
119	Electronic properties of polycrystalline graphene under large local strain. Applied Physics Letters, 2014, 104, .	1.5	17
120	2.6 μ m MBE grown InGaAs detectors with dark current of SRH and TAT. AIP Advances, 2014, 4, .	0.6	22
121	Investigation of Surface- and Buffer-Induced Current Collapse in GaN High-Electron Mobility Transistors Using a Soft Switched Pulsed (I-V) Measurement. IEEE Electron Device Letters, 2014, 35, 1094-1096.	2.2	54
122	Band offsets of non-polar A-plane GaN/AlN and AlN/GaN heterostructures measured by X-ray photoemission spectroscopy. Nanoscale Research Letters, 2014, 9, 470.	3.1	10
123	900 V/1.6 μ m Normally Off Al _{0.2} Ga _{0.8} N MOSFET on Silicon Substrate. IEEE Transactions on Electron Devices, 2014, 61, 2035-2040.	1.6	79
124	GaN-based substrates and optoelectronic materials and devices. Science Bulletin, 2014, 59, 1201-1218.	1.7	6
125	Generation and electric control of spin-valley-coupled circular photogalvanic current in WSe ₂ . Nature Nanotechnology, 2014, 9, 851-857.	15.6	278
126	Identification of Helicity-Dependent Photocurrents from Topological Surface States in Bi ₂ Se ₃ Gated by Ionic Liquid. Scientific Reports, 2014, 4, 4889.	1.6	51

#	ARTICLE	IF	CITATIONS
127	Evidence of Type-II Band Alignment in III-nitride Semiconductors: Experimental and theoretical investigation for In _{0.17} Al _{0.83} N/GaN heterostructures. Scientific Reports, 2014, 4, 6521.	1.6	23
128	Spin transport study in a Rashba spin-orbit coupling system. Scientific Reports, 2014, 4, 4030.	1.6	11
129	High-Performance Normally-Off $\text{Al}_{0.2}\text{O}_{0.3}/\text{GaN}$ MOSFET Using a Wet Etching-Based Gate Recess Technique. IEEE Electron Device Letters, 2013, 34, 1370-1372.	2.2	167
130	Deep-level traps induced dark currents in extended wavelength In _x Ga _{1-x} As/InP photodetector. Journal of Applied Physics, 2013, 114, .	1.1	43
131	Effect of Grain Boundary Scattering on Electron Mobility of N-Polarity InN Films. Applied Physics Express, 2013, 6, 021001.	1.1	13
132	Determination of the surface band bending in In _x Ga _{1-x} N films by hard x-ray photoemission spectroscopy. Science and Technology of Advanced Materials, 2013, 14, 015007.	2.8	11
133	Temperature sensitive photoconductivity observed in InN layers. Applied Physics Letters, 2013, 102, .	1.5	17
134	Effects of interface oxidation on the transport behavior of the two-dimensional-electron-gas in AlGa _N /Ga _N heterostructures by plasma-enhanced-atomic-layer-deposited AlN passivation. Journal of Applied Physics, 2013, 114, .	1.1	16
135	Fe-doped InN layers grown by molecular beam epitaxy. Applied Physics Letters, 2012, 101, 171905.	1.5	4
136	Effect of asymmetric Schottky barrier on GaN-based metal-semiconductor-metal ultraviolet detector. Applied Physics Letters, 2011, 99, .	1.5	84
137	Enhanced Device Performance of AlGa _N /Ga _N High Electron Mobility Transistors with Thermal Oxidation Treatment. Japanese Journal of Applied Physics, 2011, 50, 04DF10.	0.8	3
138	Rashba and Dresselhaus spin-orbit coupling in GaN-based heterostructures probed by the circular photogalvanic effect under uniaxial strain. Applied Physics Letters, 2010, 97, .	1.5	43
139	Enhanced wet etching of patterned GaN with heavy-ion implantation. , 2010, , .		0
140	Multiple Ti/Al stacks induced thermal stability enhancement in Ti/Al/Ni/Au Ohmic contact on AlGa _N /Ga _N heterostructure. , 2010, , .		0
141	Influence of the illumination on the subband structure and occupation in Al _x Ga _{1-x} N/GaN heterostructures. Applied Physics A: Materials Science and Processing, 2009, 96, 953-957.	1.1	1
142	Study of diffusion and thermal stability of fluorine ions in GaN by Time-of-Flight Secondary Ion Mass Spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S952-S955.	0.8	1
143	Transport and spin properties of the two-dimensional electron gas in GaN-based heterostructures. , 2008, , .		0
144	Crystalline quality of In _x Al _{1-x} N with different indium contents around lattice-matched to GaN. , 2008, , .		0

#	ARTICLE	IF	CITATIONS
145	Effect of AlN interlayer thickness on leakage currents in Schottky contacts to Al _{0.25} Ga _{0.75} N/AlN/GaN heterostructures. , 2008, , .		0
146	Magnetotransport properties of the two-dimensional electron gas in Al _x Ga _{1-x} N/GaN heterostructures under illumination. , 2008, , .		0